

EE8412

Advanced AC Drive Systems

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Counseling Hours

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Textbook: Bin Wu, 'High-Power Converters and AC Drives', Wiley-IEEE Press, 2006, ISBN: 0-471-73171-4

EE8412 Advanced AC Drive Systems

Topic 1 Introduction

- **Main Topics** (Introduction)

1. **Course Outline**
 - **Lecture Topics**
 - **Course Organization**
 - **Design Projects**
2. **Drive System Overview**
3. **Technical Requirements and Challenges**
4. **Converter Configurations**
5. **Industrial Drives**
6. **Industrial Applications**
7. **High-power Semiconductor Devices**

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Textbook: Bin Wu, 'High-Power Converters and AC Drives', Wiley-IEEE Press, 2006, ISBN: 0-471-73171-4

Topic 1 Introduction
Course Outline

- **Lecture Topics**

1. **Introduction**
2. **Induction motor dynamic models**
3. **Power Converter Topologies**
4. **Voltage Source Inverter-Fed Drives**
5. **Current Source Inverter-Fed Drives**
6. **Field Oriented control (FOC)**
7. **Direct Torque Control (DTC)**

Topic 1 Introduction
Course Outline

- **Course Organization**

Lecture 2 hours per week

Laboratory 1 hour per week (simulation)

Textbook

Bin Wu, 'High-Power Converters and AC Drive'
Wiley - IEEE Press, 2006, ISBN: 0-4717-3171-4

Lecture Slides

Download from <http://www.ee.ryerson.ca/~bwu/courses.html>

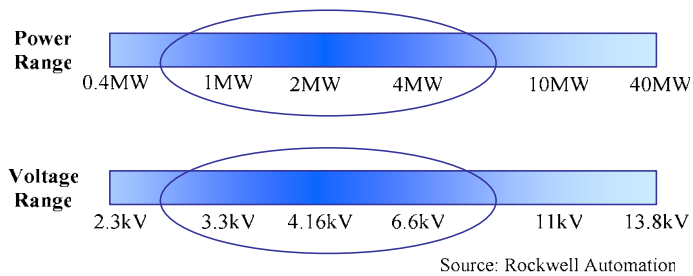
Topic 1 Introduction Course Outline

• Design Projects

1. Induction Motor Transient Characteristics	20%
2. V/F Control of Induction Motor (IM) Drive	20%
3. Field Oriented Control (FOC) of IM Drive	30%
4. Direct Torque Control (DTC) of IM Drive	30%
Total	100%

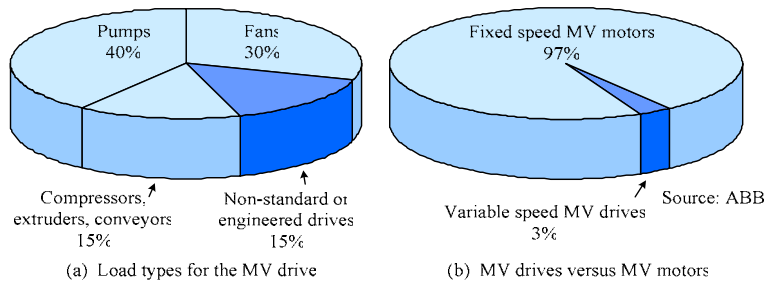
Topic 1 Introduction Drive System Overview

• Power Rating and Market Survey



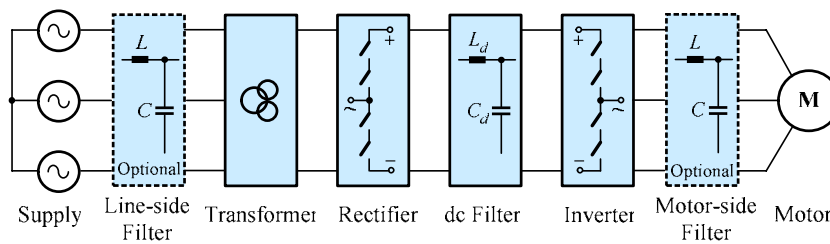
Drive System Overview

- Power Rating and Market Survey



Drive System Overview

- Drive Block Diagram



Technical Requirements and Challenges

- **Line-side Requirements**

- 1) **Line Current Distortion**

- **Causes**
 - Line current distortion is caused by rectifiers
- **Problems**
 - Nuisance tripping of computer controlled industrial processes
 - Overheating of transformers
 - Equipment failure
 - Computer data loss
 - Malfunction of communications equipment

- 2) **High Input Power Factor**

- **PF > 0.9**

Technical Requirements and Challenges

- **Line-side Requirements (Continued)**

- 3) **LC Resonance Suppression**

- **LC resonant mode**
 - Line-side filter capacitor and line inductance
- **LC resonant mode will be excited by**
 - Harmonics in supply voltages
 - Harmonics generated by the rectifier
- **Problems**
 - Overvoltages caused by the LC resonance

Technical Requirements and Challenges

• Motor-side Challenges

1) dv/dt and wave reflections

- Causes
 - Fast switching speed of semiconductor devices
 - $dv/dt > 10,000V/\mu s$
- Problems
 - Voltage doubling effect at the rising and falling edges of PWM waveforms due to wave reflections
 - Premature failure of the motor winding insulation due to partial discharges

Technical Requirements and Challenges

• Motor-side Challenges (Continued)

2) Common-mode voltage stress

- Causes
 - The switch action of the rectifier and inverter generates common-mode (CM) voltages
- Problems
 - CM voltage appears on the neutral of the stator winding with respect to ground
 - CM voltage is superimposed to the phase voltage of the the stator winding
 - Premature failure of the motor winding insulation

Technical Requirements and Challenges

- **Motor-side Challenges** (Continued)

- 3) **Motor Derating**

- **Causes**
 - Current harmonics in the stator winding.
- **Problems**
 - Additional power losses in the motor winding and magnetic core. As a consequence,
 - Motor is derated and cannot operate at its full capacity

- 4) **LC Resonances**

- 5) **Torsional Vibration**

Technical Requirements and Challenges

- **Switching Device Constraints**

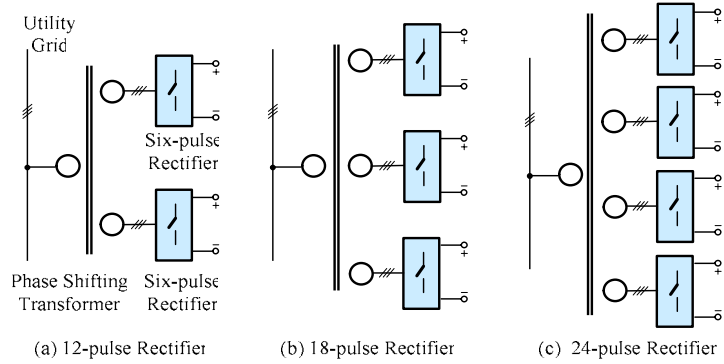
- 1) **Device Switching Frequency**
Switching frequency: < 1000Hz
Typically: 500Hz for IGCT/IGBT, 200Hz for GTO
- 2) **Series Connection**

- **Drive System Requirements**

- 1) **Low manufacturing cost**
- 2) **Small physical size**
- 3) **High reliability**
- 4) **Effective fault protection**
- 5) **Self-commissioning**
- 6) **Minimum downtime for repairs**
- 7) **High dynamic performance**

Converter Configurations

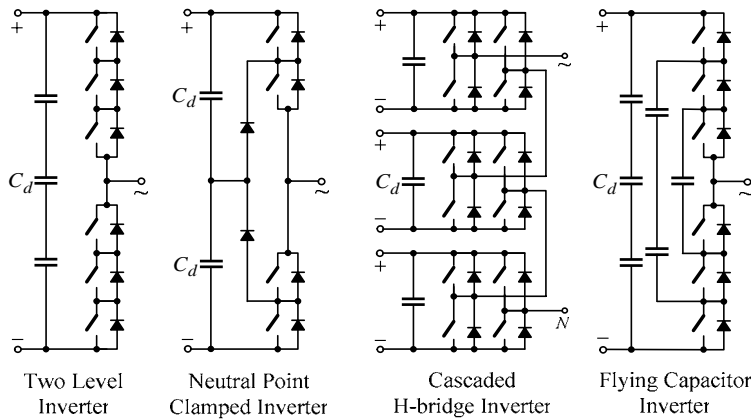
• Multipulse rectifiers



• Features: Low line current distortion

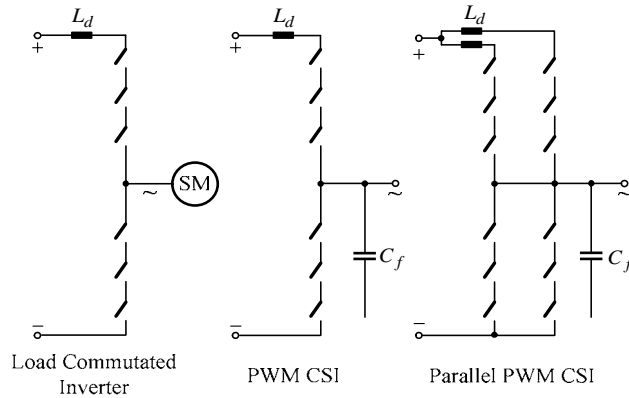
Converter Configurations

• Multilevel Voltage Source Converters



Converter Configurations

- PWM Current Source Converters



Industrial Drives

- GCT based three-level NPC inverter fed MV drive



Courtesy of ABB (ACS1000)

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Topic 1 Introduction
Industrial Drives

- IGBT-based three-level NPC inverter fed MV drive



Courtesy of Siemens (SIMOVERT MV)

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Textbook: Bin Wu, 'High-Power Converters and AC Drives', Wiley-IEEE Press, 2006, ISBN: 0-471-73171-4

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Topic 1 Introduction
Industrial Drives

- IGBT cascaded H-bridge inverter fed MV drive



Courtesy of ASI Robicon (Perfect Harmony)

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Textbook: Bin Wu, 'High-Power Converters and AC Drives', Wiley-IEEE Press, 2006, ISBN: 0-471-73171-4

Topic 1 Introduction
Industrial Drives

- CSI fed MV drive using symmetrical GCTs



Courtesy of Rockwell Automation (PowerFlex 7000)

Topic 1 Introduction
Industrial Drives

- Summary

Inverter Configuration	Switching Device	Power Range	Manufacturer
Two-Level Voltage Source Inverter	IGBT	1.4MVA – 7.2MVA	Alstom (VDM5000)
Three-Level Neutral Point Clamped Inverter	GCT	0.3MVA – 5MVA 3MVA – 27MVA	ABB (ACS1000) (ACS6000)
	GCT	3MVA – 20MVA	General Electric (Innovation Series MV-SP)
	IGBT	0.6MVA – 7.2MVA	Siemens (SIMOVERT-MV)
	IGBT	0.3MVA – 2.4MVA	General Electric–Toshiba (Dura-Bilt5 MV)
Multilevel Cascaded H-Bridge Inverter	IGBT	0.3MVA – 22MVA	ASI Robicon (Perfect Harmony)
		0.5MVA – 6MVA	Toshiba (TOSVERT-MV)
		0.45MVA – 7.5MVA	General Electric (Innovation MV-GP Type H)

Topic 1 Introduction
Industrial Drives

• **Summary (continued)**

Inverter Configuration	Switching Device	Power Range	Manufacturer
Two-Level Voltage Source Inverter	IGBT	1.4MVA – 7.2MVA	Alstom (VDM5000)
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Topic 1 Introduction
Industrial Drives

• **Summary (continued)**

NPC/H-bridge Inverter	IGBT	0.4MVA – 4.8MVA	Toshiba (TOSVERT 300 MV)
Flying-Capacitor Inverter	IGBT	0.3MVA – 8MVA	Alstom (VDM6000 Symphony)
PWM Current Source Inverter	Symmetrical GCT	0.2MVA – 20MVA	Rockwell Automation (PowerFlex 7000)
Load Commutated Inverter	SCR	>10MVA	Siemens (SIMOVERT S)
		>10MVA	ABB (LCI)
		>10MVA	Alstom (ALSPA SD7000)

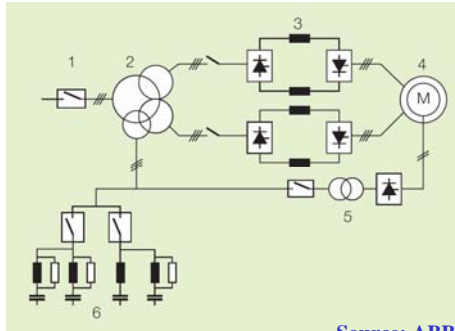
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Industrial Applications

• 100MW Wind Tunnel Drive

- Application: NASA wind tunnel
- Motor: Six-phase, synchronous
- Load: High power fan
- Speed Range: 360 - 600rpm



Source: ABB

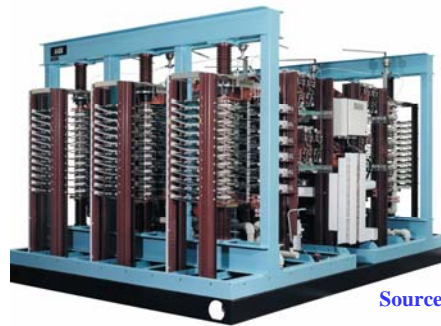
1. Supply system
2. Transformer
3. Converters
4. Motor
5. Excitation system
6. Filter

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Textbook: Bin Wu, 'High-Power Converters and AC Drives', Wiley-IEEE Press, 2006, ISBN: 0-471-73171-4

Industrial Applications

• 100MW Wind Tunnel Drive



Source: ABB

Picture of one of the 4 converters used in the drive

- Inverter type: current source
- Total # of devices: $(12 \times 6) \times 4 = 288$
- Switching device: SCR thyristor
- Converter efficiency: $> 99\%$
- # of devices in series: 12

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Topic 1 Introduction
Industrial Applications

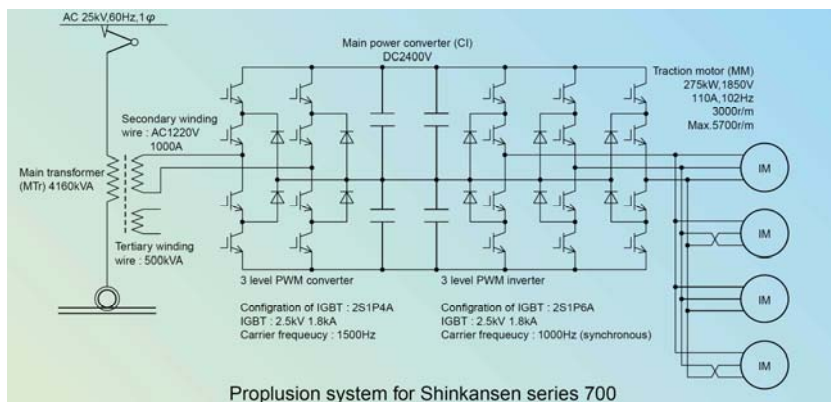
• **High Speed Train**



Source: Fuji Electric

Topic 1 Introduction
Industrial Applications

• **High Speed Train**



Source: Fuji Electric

Rectifier: Single-phase three-level diode clamped
Inverter: Three-phase three-level diode clamped
Ratings: 1.1MW, 1850V

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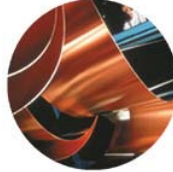
Topic 1 Introduction Industrial Applications



Mining / cement



Petrochemical



Iron / steel



Paper / pulp



Marine



Oil / gas



Power generation



Water / waste water

Source: Robicon

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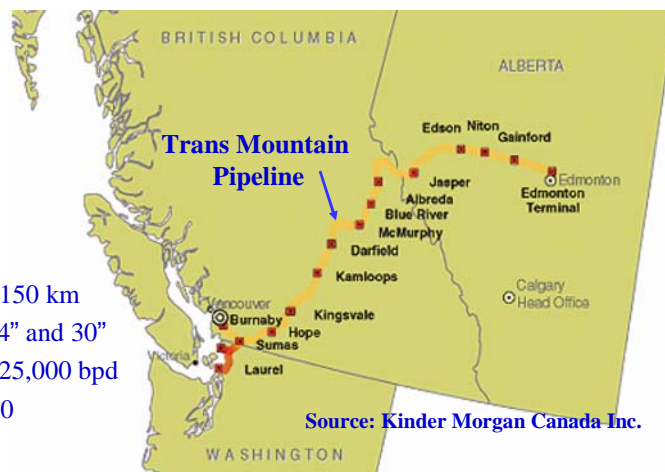
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Topic 1 Introduction Industrial Applications

• Megawatt Drive for Pipeline Pumps

Length: 1,150 km
Pipe Size: 24" and 30"
Capacity: 225,000 bpd
Pump stations: 10



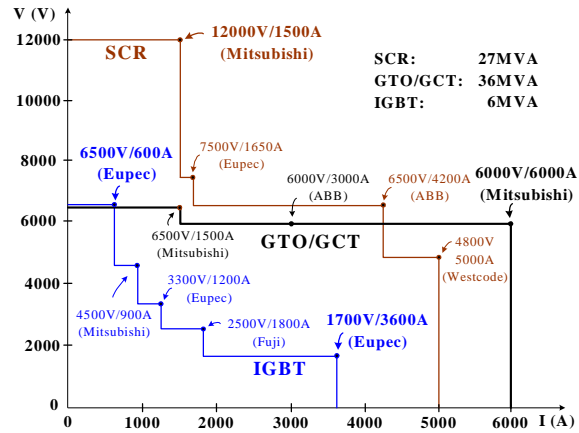
Source: Kinder Morgan Canada Inc.

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High-Power Semiconductor Devices

• Device Ratings



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High-Power Semiconductor Devices

• Diode



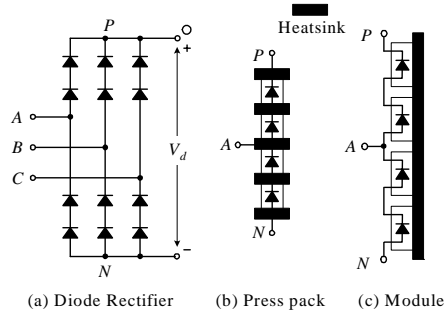
4500V/800A press pack and 1700V/1200A module diodes

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High-Power Semiconductor Devices

• Heatsink Assembly



Press pack device:

- Double sided cooling
- Low assembly cost and high power density
- Preferred choice for high voltage high power applications

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High-Power Semiconductor Devices

• SCR – Silicon Controlled Rectifier



4500V/800A and 4500V/1500A SCRs

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High-Power Semiconductor Devices

• Gate Turn-Off (GTO) Thyristor



4500V/800A and 4500V/1500A GTOs

High-Power Semiconductor Devices

• Symmetrical *versus* Asymmetrical GTOs

Type	Blocking Voltage	Example (6000V GTOs)	Applications
Asymmetrical GTO	$V_{RRM} \ll V_{DRM}$	$V_{DRM} = 6000V$ $V_{RRM} = 22V$	For use in voltage source inverters with anti-parallel diodes.
Symmetrical GTO	$V_{RRM} \approx V_{DRM}$	$V_{DRM} = 6000V$ $V_{RRM} = 6500V$	For use in current source inverters.

V_{DRM} - Maximum repetitive peak (forward) off-state voltage

V_{RRM} - Maximum repetitive peak reverse voltage

High-Power Semiconductor Devices

• GTO Specifications

4500V/4000A Asymmetrical GTO Thyristor

Maximum Rating	V_{DRM}	V_{RRM}	I_{TGQM}	I_{TAVM}	I_{TRMS}	-
	4500V	17V	4000A	1000A	1570A	-
Switching Characteristics	Turn-on Switching	Turn-off Switching	di_T/dt	dv_T/dt	di_{G1}/dt	di_{G2}/dt
	$t_{don} = 2.5\mu s$	$t_{doff} = 25.0\mu s$	500A / μs	1000V / μs	40A / μs	40A / μs
	$t_r = 5.0\mu s$	$t_f = 3.0\mu s$				
On-state Voltage	$V_{T(on-state)} = 4.4V$ at $I_T = 4000A$					
V_{DRM} - Repetitive peak off-state voltage			V_{RRM} - Repetitive peak reverse voltage			
I_{TGQM} - Repetitive controllable on-state current			I_{TAVM} - Maximum average on-state current			
I_{RRMS} - Maximum rms on-state current			Part number - 5SGA 40L4501 (ABB)			

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High-Power Semiconductor Devices

• Integrated Gate Commutated Thyristor (GCT)



6500V/1500A Symmetrical GCT

GCT = Improved GTO + Integrated Gate + Anti-parallel Diode (optional)

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High-Power Semiconductor Devices

• GCT Classifications

Type	Anti-parallel Diode	Blocking Voltage	Example (6000V GCT)	Applications
Asymmetrical GCT	Excluded	$V_{RRM} \ll V_{DRM}$	$V_{DRM} = 6000V$ $V_{RRM} = 22V$	For use in voltage source inverters with anti-parallel diodes.
Reverse Conducting GCT	Included	$V_{RRM} \approx 0$	$V_{DRM} = 6000V$	For use in voltage source inverters.
Symmetrical GCT (Reverse Blocking)	Not required	$V_{RRM} \approx V_{DRM}$	$V_{DRM} = 6000V$ $V_{RRM} = 6500V$	For use in current source Inverters.

V_{DRM} - Maximum repetitive peak forward off-state voltage
 V_{RRM} - Maximum repetitive peak reverse voltage

High-Power Semiconductor Devices

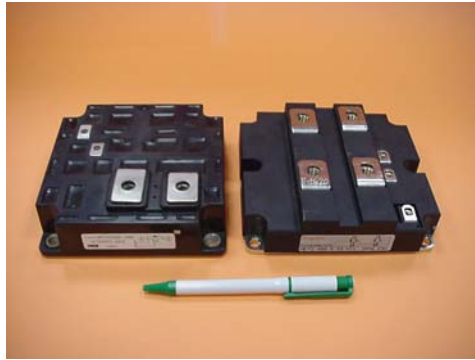
• GCT Specifications

6000V/6000A Asymmetrical GCT

Maximum Rating	V_{DRM}	V_{RRM}	I_{TORM}	I_{TAVM}	I_{TRMS}	-
	6000V	22V	6000A	2000A	3100A	-
Switching Characteristics	Turn-on Switching	Turn-off Switching	di_T/dt	dv_T/dt	di_{G1}/dt	di_{G2}/dt
	$t_{don} < 1.0\mu s$ $t_r < 2.0\mu s$	$t_{doff} < 3.0\mu s$ $t_f - N/A$	1000A / μs	3000V / μs	200A / μs	10,000 A / μs
On-state Voltage	$V_{T(on-state)} < 4V$ at $I_T = 6000A$					
V_{DRM} - Repetitive peak off-state voltage			V_{RRM} - Repetitive peak reverse voltage			
I_{TORM} - Repetitive controllable on-state current			I_{TAVM} - Maximum average on-state current			
I_{RRMS} - Maximum rms on-state current			Part number – FGC6000AX120DS (Mitsubishi)			

High-Power Semiconductor Devices

• Insulated Gate Bipolar Transistor (IGBT)



1700V/1200A and 3300V/1200A IGBT modules

High-Power Semiconductor Devices

• IGBT Specifications

3300V/1200A IGBT

Maximum Rating	V_{CE}	I_C	I_{CM}	-
	3300V	1200A	2400A	-
Switching Characteristics	t_{don}	t_r	t_{doff}	t_f
	$0.35\mu s$	$0.27\mu s$	$1.7\mu s$	$0.2\mu s$
Saturation Voltage	$I_{CE sat} = 4.3V$ at $I_C = 1200A$			
V_{CE} - Rated collector-emitter voltage I_C - Rated dc collector current I_{CM} - Maximum repetitive peak collector current Part number – FZ1200 R33 KF2 (Eupec)				

High-Power Semiconductor Devices

• Comparison

Item	GTO	IGCT	IGBT
Maximum switch power (Device $V \times I$)	36MVA	36MVA	6MVA
Active di/dt and dv/dt control	No	No	Yes
Active short circuit protection	No	No	Yes
Turn-off (dv/dt) snubber	Required	Not required	No required
Turn-on (di/dt) snubber	Required	Required	No required
Parallel connection	No	No	Yes
Switching speed	Slow	Moderate	Fast
Behavior after destruction	Shorted	Shorted	Open in most cases
On-state losses	Low	Low	High
Switching losses	High	Low	Low
Gate Driver	Complex, separate	Complex, integrated	Simple, compact
Gate Driver Power Consumption	High	High	Low

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Topic 1 Introduction

Thanks

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